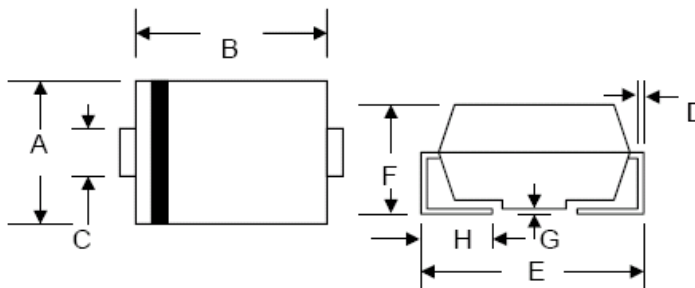




Technical Data
Data Sheet N0440, Rev. -

Features

- Glass Passivated Die Construction
- Ideally Suited for Automatic Assembly
- Low Forward Voltage Drop, High Efficiency
- Surge Overload Rating to 100A Peak
- Low Power Loss
- Fast Recovery Time
- Plastic Case Material has UL Flammability Classification Rating 94V-O
- This is a Pb - Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request



SMC/DO-214AB				
Dim	Min	Max	Min	Max
A	5.59	6.22	0.220	0.245
B	6.60	7.11	0.260	0.280
C	2.75	3.25	0.108	0.128
D	0.152	0.305	0.006	0.012
E	7.75	8.13	0.305	0.320
F	2.00	2.62	0.079	0.103
G	0.051	0.203	0.002	0.008
H	0.76	1.27	0.030	0.05
			In mm	In inch

Mechanical Data

- Case: Molded Plastic
- Terminals: Solder Plated, Solderable per MIL-STD-750, Method 2026
- Polarity: Cathode Band or Cathode Notch
- Marking: Type Number
- Weight: 0.21 grams (approx.)

Marking Diagram:

Where XXXXX is YYWWL



FR3A = Part Name
YY = Year
WW = Week
L = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Ordering Information

Device	Package	Shipping
FR3A-FR3K	SMC (Pb-Free)	3000pcs / reel

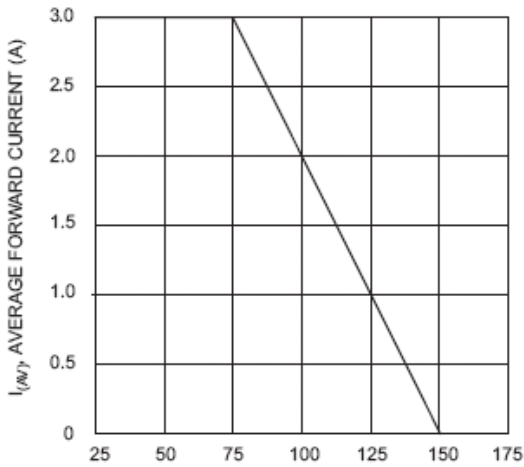
For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.



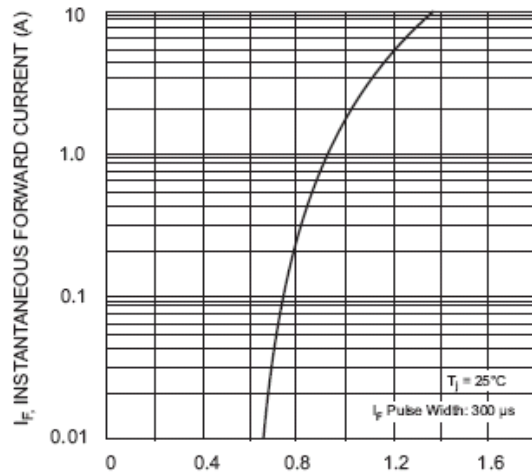
Maximum Ratings and Electrical Characteristics @ $T_A=25^{\circ}\text{C}$ unless otherwise specified

Characteristic	Symbol	FR3A	FR3B	FR3D	FR3G	FR3J	FR3K	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	200	400	600	800	V
RMS Reverse Voltage	$V_{R(RMS)}$	35	70	140	280	420	560	V
Average Rectified Output Current @ $T_L = 75^{\circ}\text{C}$	I_o	3.0						A
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	100						A
Forward Voltage @ $I_F = 3.0\text{A}$	V_{FM}	1.30						V
Peak Reverse Current @ $T_A = 25^{\circ}\text{C}$ At Rated DC Blocking Voltage @ $T_A = 125^{\circ}\text{C}$	I_{RM}	10 350						μA
Reverse Recovery Time (Note 1)	t_{rr}	150				250	500	nS
Typical Junction Capacitance (Note 2)	C_j	60						pF
Typical Thermal Resistance (Note 3)	$R_{\theta JL}$	15						K/W
Operating and Storage Temperature Range	T_j, T_{STG}	-50 to +150						$^{\circ}\text{C}$

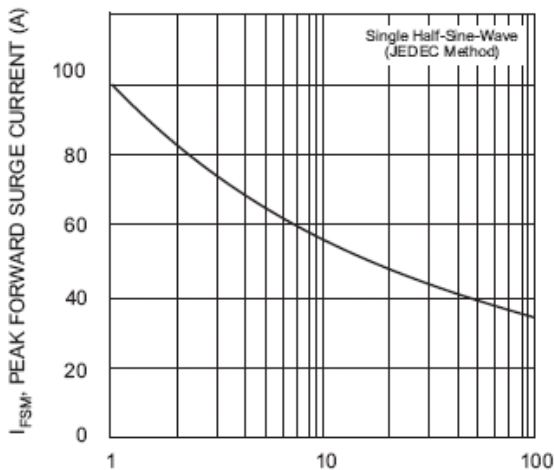
Note: 1. Measured with $I_F = 0.5\text{A}$, $I_R = 1.0\text{A}$, $I_{rr} = 0.25\text{A}$,
2. Measured at 1.0 MHz and applied reverse voltage of 4.0 V DC.
3. Mounted on P.C. Board with 8.0mm^2 land area.



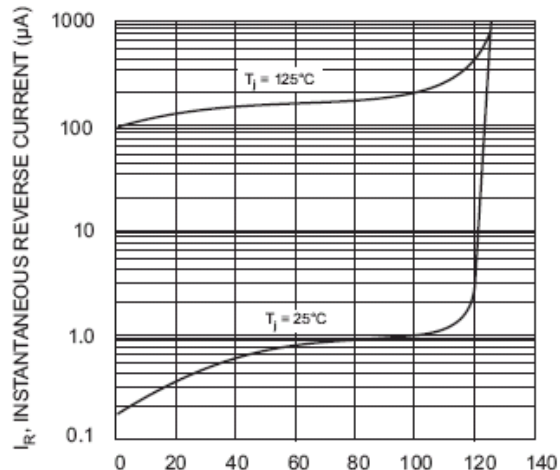
T_L , LEAD TEMPERATURE ($^{\circ}$ C)
Fig. 1 Forward Current Derating Curve



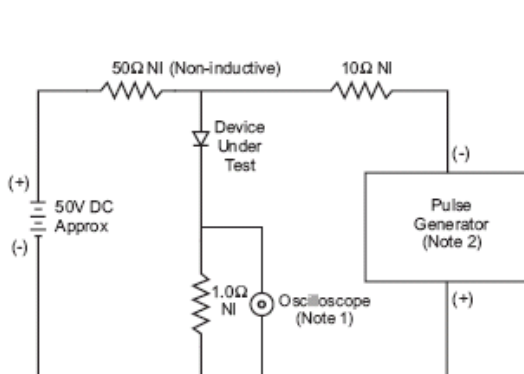
V_F , INSTANTANEOUS FORWARD VOLTAGE (V)
Fig. 2 Typical Forward Characteristics



NUMBER OF CYCLES AT 60 Hz
Fig. 3 Forward Surge Current Derating Curve



PERCENT OF RATED PEAK REVERSE VOLTAGE (%)
Fig. 4 Typical Reverse Characteristics



Notes:
1. Rise Time = 7.0ns max. Input Impedance = 1.0M Ω , 22pF.
2. Rise Time = 10ns max. Input Impedance = 50 Ω .

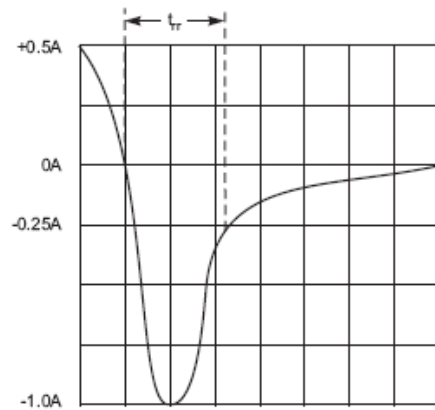


Fig. 5 Reverse Recovery Time Characteristic and Test Circuit



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